1.52mm×1.52mm Silicon PD Chip datasheet

P/N：WS9L-01A

Application

Si PIN photodiode chips

Structure

Planar type：PIN diode

Electrodes ：

Top side（Cathode）: Al

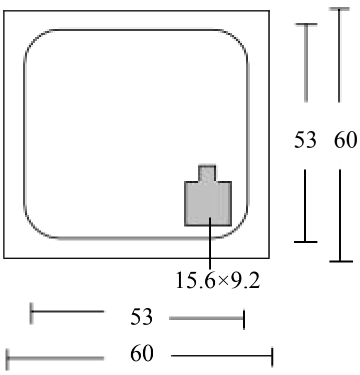
Backside（Anode） ：Au Alloy

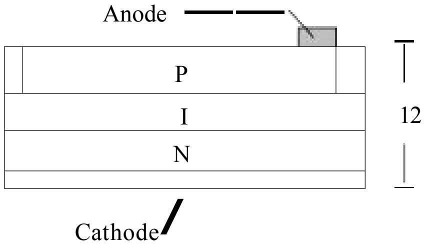
DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	53 × 53			mil
Chip width	60 × 60 （± 1.0）			mil
Chip length	60 × 60 （± 1.0）			mil
Chip height	12 （± 1.0）			mil
Pad N(Cathode)	15.6 × 9.2			mil
Pad P(Anode)	15.6 × 9.2			mil

Electro-Optical Characteristics（@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=10mA, H=0	0.7		1.3	V
Reverse Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Sensitive Wavelength Range	λp			940		nm
Capacitance	CJ	VR=3V, F=1 MHz		11		pF





Unit:mil

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